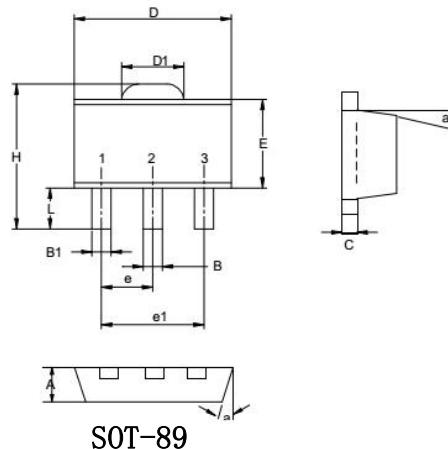


## Features

- Low On resistance.
- -4.5V drive.
- Lead Free and Green Devices Available (RoHS compliant) .



## Package Dimensions



## Specifications

### Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	$V_{DSS}$		-30	V
Gate-to-Source Voltage	$V_{GSS}$		$\pm 20$	V
Drain Current (DC)	$I_D$		-5.0	A
Drain Current (Pulse)	$I_{DP}$	$PW \leq 10\mu\text{s}$ , duty cycle $\leq 1\%$	-20	A
Allowable Power Dissipation	$P_D$	Mounted on a ceramic board ( $1000\text{mm}^2 \times 0.8\text{mm}$ ) 1unit	1.3	W
Total Dissipation	$P_T$	Mounted on a ceramic board ( $1000\text{mm}^2 \times 0.8\text{mm}$ )	1.7	W
Channel Temperature	$T_{ch}$		150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$		-55~+150	$^\circ\text{C}$

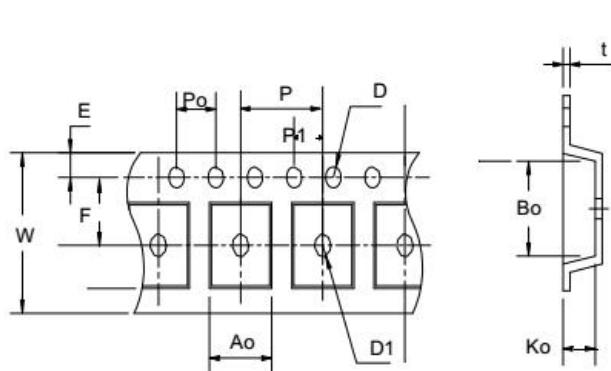
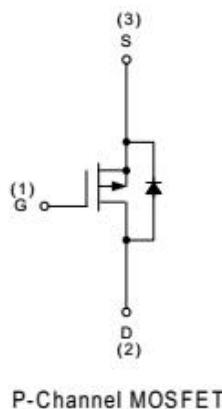
### Electrical Characteristics at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=-250\mu\text{A}$ , $V_{GS}=0\text{V}$	-30			V
Zero-Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-30\text{V}$ , $V_{GS}=0\text{V}$			-1	$\mu\text{A}$
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20\text{V}$ , $V_{DS}=0\text{V}$			$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_D=-250\mu\text{A}$	-1.0		-3.0	V
Static Drain-to-Source On-State Resistance	$R_{DS(ON)}$	$I_D=-5.0\text{A}$ , $V_{GS}=-10\text{V}$		47	60	$\text{m}\Omega$
	$R_{DS(ON)}$	$I_D=-4\text{A}$ , $V_{GS}=-4.5\text{V}$		75	95	$\text{m}\Omega$
Input Capacitance	$C_{iss}$	$V_{DS}=-15\text{V}$ , $V_{GS}=0\text{V}$ , $f=1\text{MHz}$		680		pF
Output Capacitance	$C_{oss}$	$V_{DS}=-15\text{V}$ , $V_{GS}=0\text{V}$ , $f=1\text{MHz}$		120		pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS}=-15\text{V}$ , $V_{GS}=0\text{V}$ , $f=1\text{MHz}$		75		pF

## Electrical Characteristics at $T_a=25^{\circ}\text{C}$ (Continued)

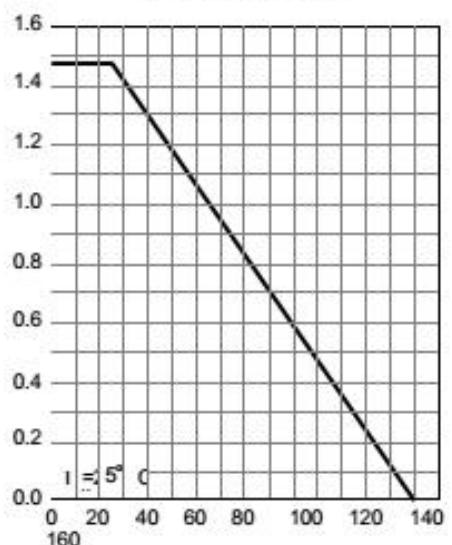
Parameter	Symbol	Conditions	Ratings			Unit
			min	Typ	max	
Turn-on Delay Time	$t_{d(on)}$	$V_{\text{GEN}}=-10\text{V}, V_{\text{DS}}=-15\text{V}, R_{\text{L}}=15\Omega,$ $I_{\text{D}}=-1\text{A}, R_{\text{GEN}}=6\Omega$		7.0	15	nS
Rise Time	$t_r$			10	20	nS
Turn-off Delay Time	$t_{d(off)}$			40	80	nS
Fall Time	$t_f$			20	40	nS
Total Gate Charge	$Q_g$	$V_{\text{DS}}=-15\text{V}, V_{\text{GS}}=-10\text{V}, I_{\text{D}}=5\text{A}$		10	15	nC
Gate-to-Source Charge	$Q_{gs}$			4.0		nC
Gate-to-Drain "Miller" Charge	$Q_{gd}$			2.0		nC
Diode Forward Voltage	$V_{SD}$	$I_{\text{S}}=-2\text{A}, V_{\text{GS}}=0\text{V}$		-0.8	-1.2	V

## Pin Description



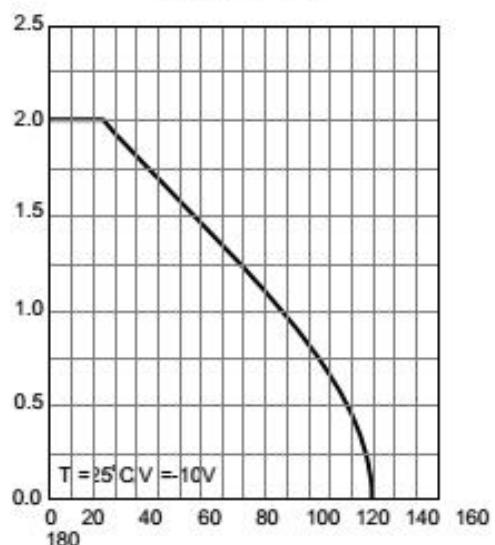
## Typical Characteristics at $T_a=25^{\circ}\text{C}$

**Power Dissipation**



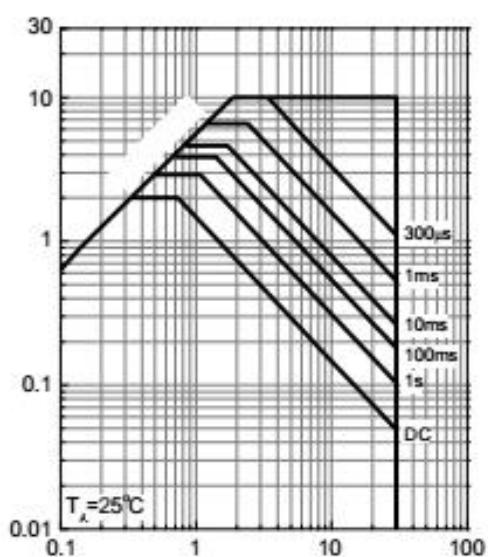
$T_j$  - Junction Temperature (°C)

**Drain Current**



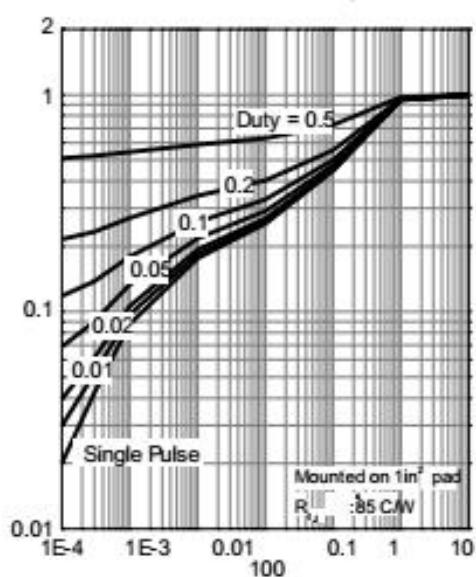
$T_j$  - Junction Temperature

**Safe Operation Area**



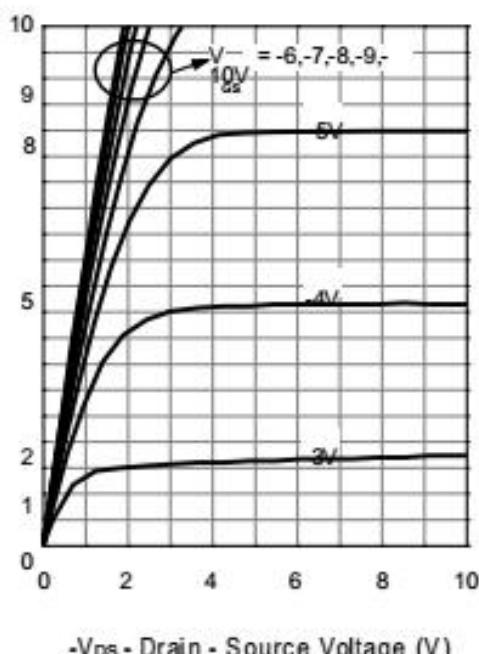
$-V_{DS}$  - Drain - Source Voltage (V)

**Thermal Transient Impedance**



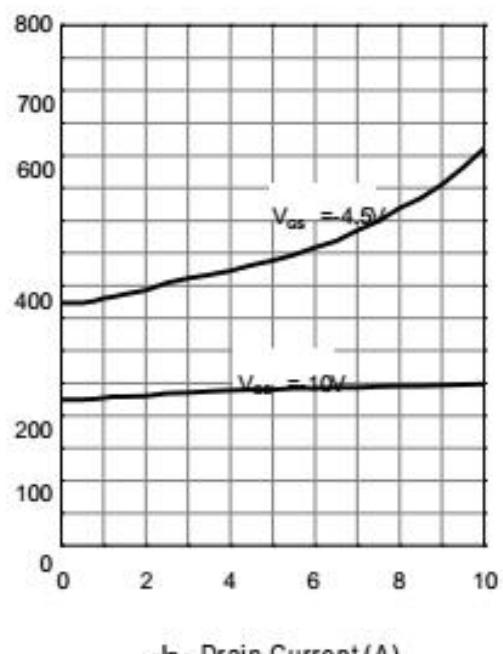
Square Wave Pulse Duration (sec)

Output Characteristics



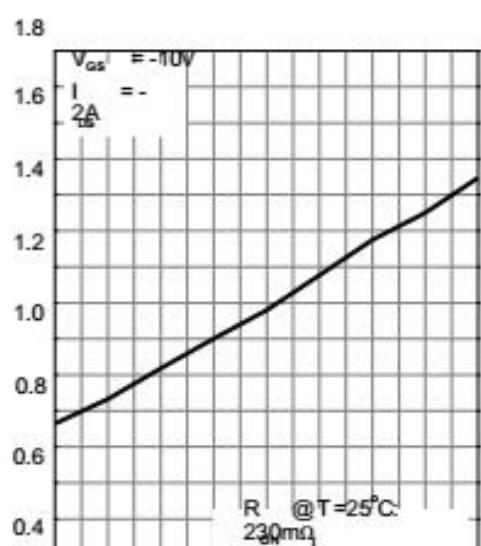
- $V_{DS}$  - Drain - Source Voltage (V)

Drain-Source On Resistance



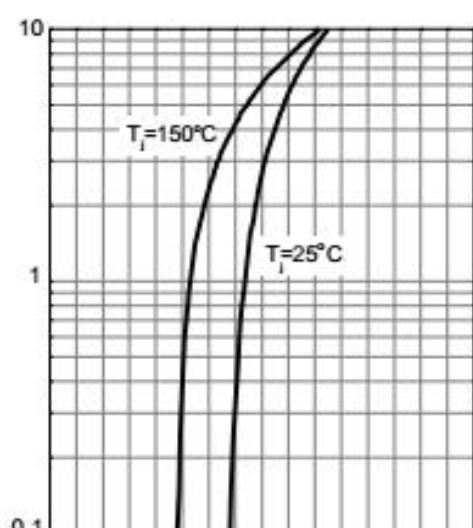
- $I_D$  - Drain Current (A)

Drain-Source On Resistance



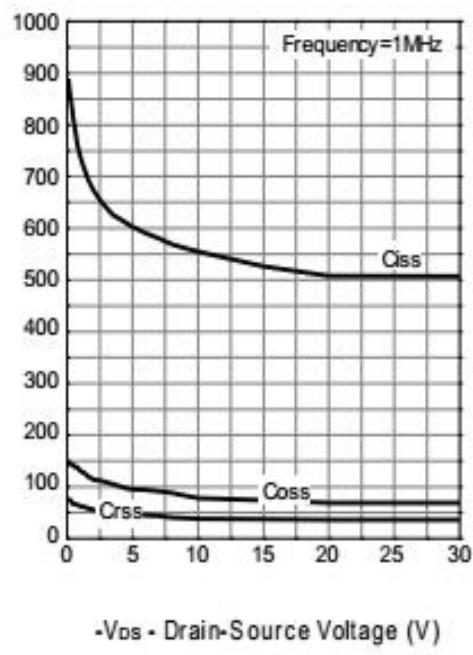
$T_J$  - Junction Temperature (°C)

Source-Drain Diode Forward



- $V_{SD}$  - Source - Drain Voltage (V)

Capacitance



Gate Charge

